



JMSL1018PP

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% Vds Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

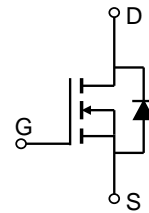
Parameters	Value	Unit
V_{DSS}	100	V
$V_{GS(th_Typ)}$	1.7	V
$I_D(@V_{GS}=10V)$	8.4	A
$R_{DS(ON_Typ)}(@V_{GS}=10V)$	14.7	mΩ
$R_{DS(ON_Typ)}(@V_{GS}=4.5V)$	22.2	mΩ



SOP-8



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSL1018PP-13	SL1018P	3	Tape&Reel	SOP-8	4000	48000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	8.4
		$T_A = 100^\circ\text{C}$	5.3
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	74	mJ
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	2.5
		$T_A = 100^\circ\text{C}$	1.0
T_{J_STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
R	Thermal Resistance, Junction to Ambient ⁽³⁾	50	$^\circ\text{C/W}$



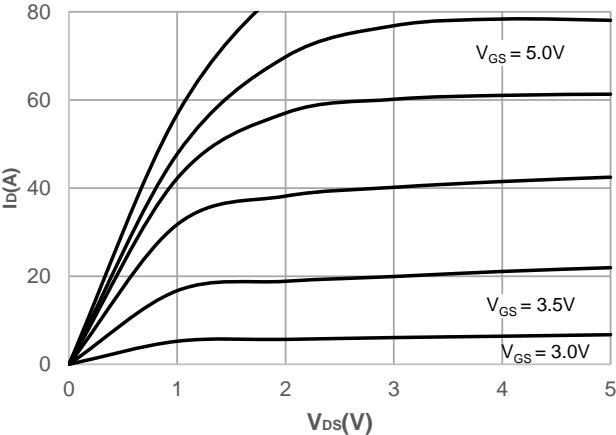
Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics					
V _{(BR)DSS}		100	-	-	V
I _{DSS}		-	-	1.0	P
I _{GSS}		-	-	±100	
<hr/>					
V _{GS(th)}		1.2	1.7	2.2	V
		-	14.7	19.1	m :
		-	22.2	28.9	m :
<hr/>					
R _g		-	2	-	:
C _{iss}		-	707	1061	pF
C _{oss}		-	357	535	pF
C _{rss}		-	9	-	pF
Q _g		-	13	-	nC
Q _{gs}		-	2.8	-	nC
Q _{gd}		-	2.9	-	nC
<hr/>					
t _{d(on)}		-	6.4	-	ns
t _r		-	27	-	ns
t _{d(off)}		-	18	-	ns
t _f		-	8.0	-	ns
<hr/>					
I _S		-	-	8.4	A
I _{SM}		-	-	34	A
V _{SD}		-	-	1.2	V
trr		23	38	58	ns
Qrr		-	21	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting T_J

Typical Performance Characteristics

Figure 5: Output Characteristics





Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

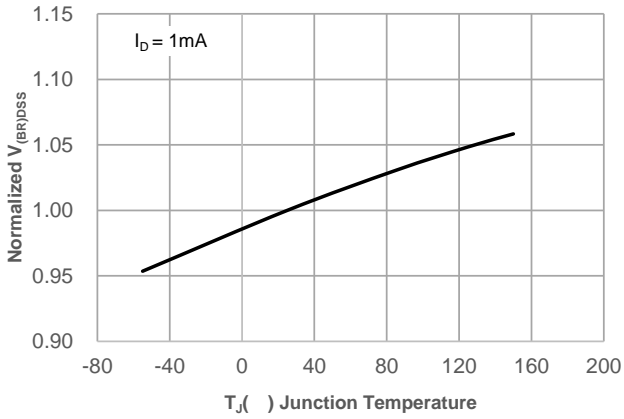


Figure 12: Normalized on Resistance vs. Junction Temperature

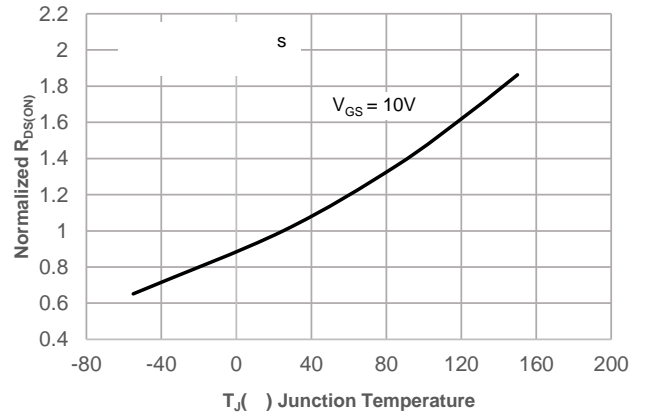


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

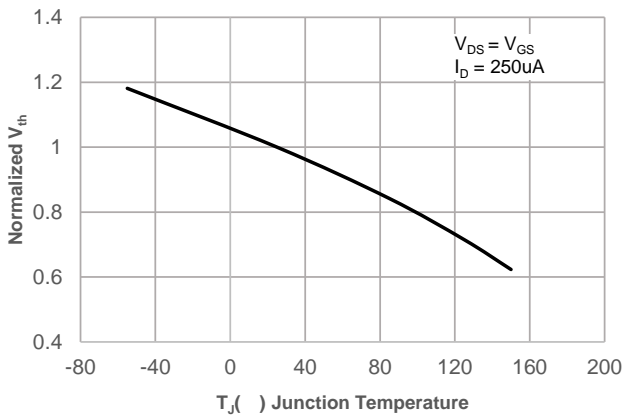


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

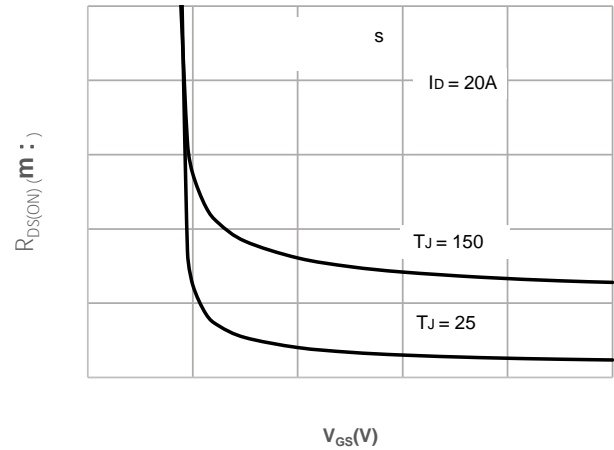
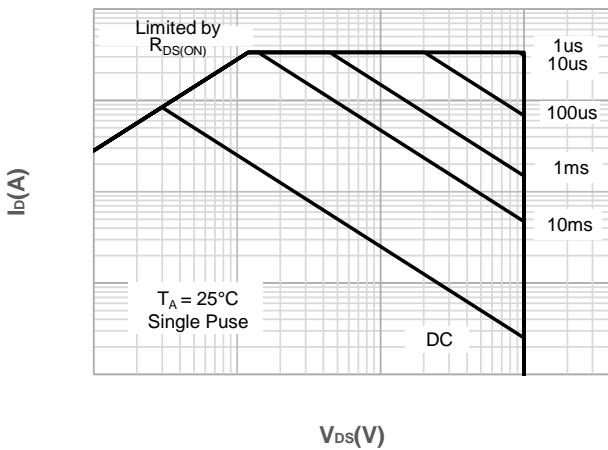


Figure 15: Maximum Safe Operating Area



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

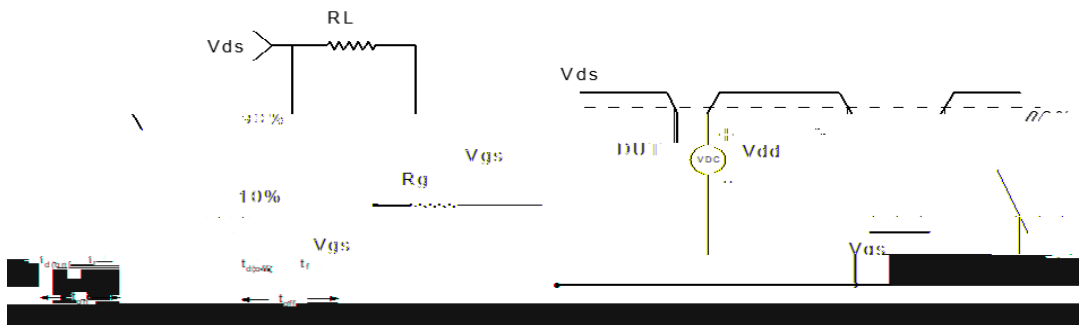


Figure 2: Resistive Switching Test Circuit & Waveform

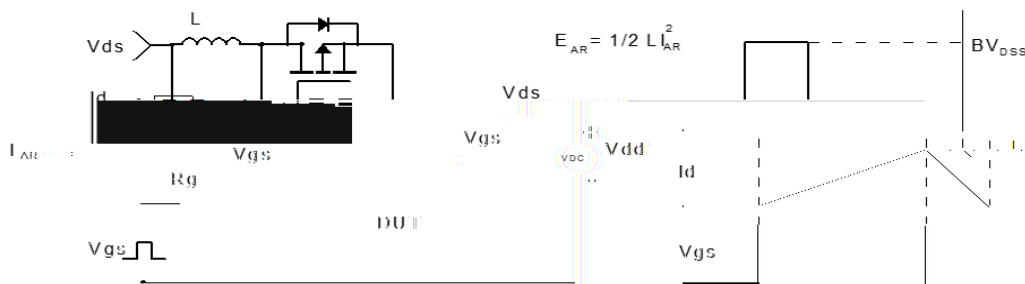


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

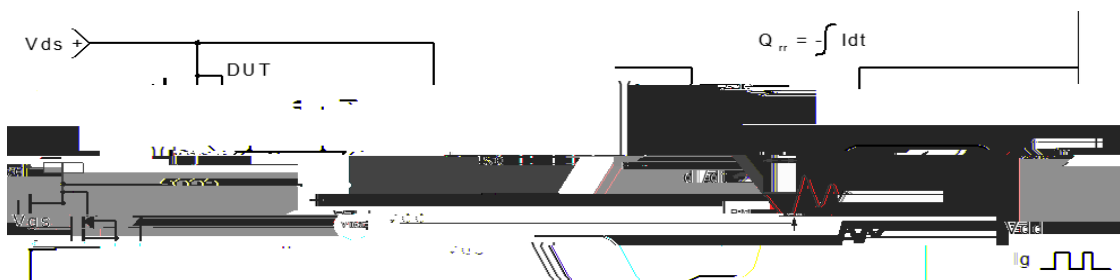


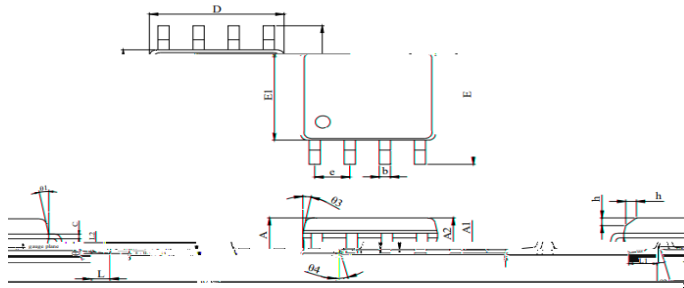
Figure 4: Diode Recovery Test Circuit & Waveform





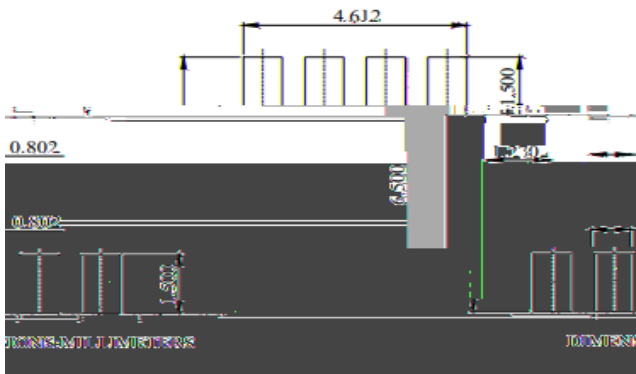
Package Mechanical Data(SOP-8)

Package Outline



DIM	MILLIMETER		
	MIN.	NOM.	MAX.
A	1.35	1.50	1.65
A1	0.05	0.10	0.15
A2	1.35	1.40	1.50
b	0.38	--	0.50
c	0.17	--	0.25
D	4.80	4.90	5.00
E	5.80	6.00	6.20
e	3.80	3.90	4.00
e1	1.27(BSC)		
e2	0.45	0.60	0.80
e3	1.04 REF		
e4	0.25 BSC		
e5	0.30	0.40	0.50
θ1	0°	--	8°
θ2	10°	12°	14°
θ3	8°	10°	12°
θ4	10°	12°	14°
θ5	8°	10°	12°

Recommended Footprint



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